

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: To Be Assigned
Examiner: To Be Assigned

In Re PATENT APPLICATION OF:

Applicants : Toyokazu Sakata

Serial No. : To Be Assigned

Filed : November 26, 2003

For : ETCHING METHOD AND
SEMICONDUCTOR DEVICE
FABRICATING METHOD

Attorney Ref. : TAI 145

INFORMATION
DISCLOSURE
STATEMENT

November 26, 2003

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(1).


Attached are copies of two Japanese patent publications and two English -language publications. Any relevance of the Japanese patents can be gleaned from the attached English-language Abstracts. The one of the Japanese publications and both English-language publications are listed on the attached Form PTO-1449 and discussed on pages 2 and 3 of the application. Also listed on the form PTO-1449 for consideration is one U.S. Patent. As the present application was filed after June 30, 2003, a copy of the U.S. Patent is not submitted with the Information Disclosure Statement, pursuant to the Notice of U.S. Patent & Trademark Office posted on the USPTO website on July 11, 2003.

Since this Information Disclosure Statement is being filed with the application, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to the documents submitted. Consideration of the submitted and listed documents is respectfully requested.

Respectfully submitted,

November 26, 2003
Date

SMR:tl


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| FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT | | | | Atty Docket | | Application No. | |
| | | | | TAI 145 | | To Be Assigned | |
| | | | | Applicant | | | |
| | | | | Toyokazu Sakata | | | |
| Filing Date | | | | Group Unit | | | |
| November 26, 2003 | | | | To Be Assigned | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| Examiner Initial | | Document Number | Date | Name | Class | Sub-Class | Filing Date |
| | AA | 6,355,572 | 03/12/02 | Ikegami | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
| | AE | | | | | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | Document Number | Date | Country | Class | Sub-Class | Translation |
| | AK | 7-94483 | 04/07/95 | Japan | | | Abstract |
| | AL | 2001-77086 | 03/23/01 | Japan | | | Abstract |
| | AM | | | | | | |
| | AN | | | | | | |
| OTHER (Including Author, Title, Date, Pertinent Pages, etc.) | | | | | | | |
| | AO | "Dry Etching of Organic Low Dielectric Constant Film without Etch Stop Layer" M.Mizumura et al. JJAP, Vol. 41, pp. 425-427 | | | | | |
| | AP | "Highly Selective Etching of Organic SOG to SiN for Cu Damascene Interconnects Using New Gas Chemistry of C₄F₈/N₂/Ar" S. Uno et al. Proc. Of Dry Process Symp., pp. 215-220(1999) | | | | | |
| | AQ | | | | | | |
| Examiner | | | | | Date Considered | | |
| EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant. | | | | | | | |